Xin Chen

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/4598288/publications.pdf

Version: 2024-02-01

11	210	1163117 8	1281871 11
papers	citations	h-index	g-index

11	11	11	187
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Improved minority carrier lifetime in p-type GaN by suppressing the non-radiative recombination process. Applied Physics Express, 2022, 15, 075501.	2.4	5
2	Influence of Mg doping level at the initial growth stage on the gate reliability of p-GaN gate HEMTs. Journal Physics D: Applied Physics, 2022, 55, 355103.	2.8	3
3	Gate Reliability and its Degradation Mechanism in the Normally OFF High-Electron-Mobility Transistors With Regrown p-GaN Gate. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 3715-3724.	5.4	8
4	High-Voltage and High-I_{ON}/I_{OFF} Quasi-Vertical GaN-on-Si Schottky Barrier Diode With Argon-Implanted Termination. IEEE Electron Device Letters, 2021, 42, 473-476.	3.9	37
5	Reverse leakage and breakdown mechanisms of vertical GaN-on-Si Schottky barrier diodes with and without implanted termination. Applied Physics Letters, 2021, 118, .	3.3	26
6	Influence of the carrier behaviors in p-GaN gate on the threshold voltage instability in the normally off high electron mobility transistor. Applied Physics Letters, 2021, 119, .	3.3	14
7	Influence of traps on the gate reverse characteristics of normally-off high-electron-mobility transistors with regrown p-GaN gate. Applied Physics Express, 2021, 14, 104005.	2.4	3
8	Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm². IEEE Transactions on Electron Devices, 2021, 68, 5682-5686.	3.0	24
9	Determination of carbon-related trap energy level in (Al)GaN buffers for high electron mobility transistors through a room-temperature approach. Applied Physics Letters, 2020, 117, .	3.3	18
10	Normally-off HEMTs With Regrown p-GaN Gate and Low-Pressure Chemical Vapor Deposition SiN_x Passivation by Using an AlN Pre-Layer. IEEE Electron Device Letters, 2019, 40, 1495-1498.	3.9	50
11	Effect of Thermal Cleaning Prior to p-GaN Gate Regrowth for Normally Off High-Electron-Mobility Transistors. ACS Applied Materials & Interfaces, 2019, 11, 21982-21987.	8.0	22